

# S-82B4A/5A Series

# BATTERY PROTECTION IC FOR 4-SERIAL OR 5-SERIAL CELL PACK

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This IC is a protection IC for lithium-ion rechargeable batteries, which includes high-accuracy voltage detection circuits and delay circuits. It is suitable for protecting 4-serial or 5-serial cell lithium-ion rechargeable battery packs from overcharge, overdischarge, and overcurrent.

# Features

High-accuracy voltage detection for each cell		
Overcharge detection voltage n	3.900 V to 4.500 V (25 mV step)	Accuracy ±20 mV
Overcharge release voltage n	3.500 V to 4.500 V*1	Accuracy ±50 mV
Overdischarge detection voltage n	2.000 V to 3.200 V (100 mV step)	Accuracy ±50 mV
Overdischarge release voltage n	2.000 V to 3.400 V*2	Accuracy ±100 mV
Three-level discharge overcurrent detection		
Discharge overcurrent 1 detection voltage	10 mV to 200 mV (5 mV step)	Accuracy ±5 mV
Discharge overcurrent 2 detection voltage	20 mV to 300 mV (5 mV step)	Accuracy ±10 mV
Load short-circuiting detection voltage	50 mV to 400 mV (10 mV step)	Accuracy ±20 mV
Charge overcurrent detection		
Charge overcurrent detection voltage	–200 mV to –10 mV (5 mV step)	Accuracy $\pm 5 \text{ mV}$
• Discharge overcurrent 1 detection delay time is set	table by an external capacitor (The	other delay time are internally
fixed)		
<ul> <li>Power saving control by a control pin</li> </ul>		
0 V battery charge:	Enabled, inhibited	
Power-down function:	Available, unavailable	
• Release condition of discharge overcurrent status:	Load disconnection, charg	ger connection
• Output voltage of CO and DO pin is limited to VC2 p	in voltage. (S-82B5A Series)	-
High-withstand voltage:	Absolute maximum rating	28.0 V
Wide operating voltage range:	5.0 V to 24.0 V	
Wide operation temperature range:	Ta = -40°C to +85°C	
Low current consumption		
During operation:	4.0 μA typ., 8.0 μA max. (	(Ta = +25°C)
During power-down:	$0.1 \mu\text{A} \text{ max}.$ (Ta = +25°C)	· ,
During power-saving:	$0.1 \mu\text{A} \text{ max.} (\text{Ta} = +25^{\circ}\text{C})$	
<ul> <li>Lead-free (Sn 100%), halogen-free</li> </ul>	$0.1  \mu$ (10 – 120 0)	
*1. Overcharge release voltage = Overcharge detection	on voltage – Overcharge hysteresis	voltage
(Overcharge hysteresis voltage n can be selected		-

(Overcharge hysteresis voltage n can be selected from a range of 0 V to 0.4 V in 50 mV steps.)
\*2. Overdischarge release voltage = Overdischarge detection voltage + Overdischarge hysteresis voltage (Overdischarge hysteresis voltage n can be selected from a range of 0 V to 0.7 V in 100 mV steps.)

### **Remark** n = 1, 2, 3, 4, 5

# Applications

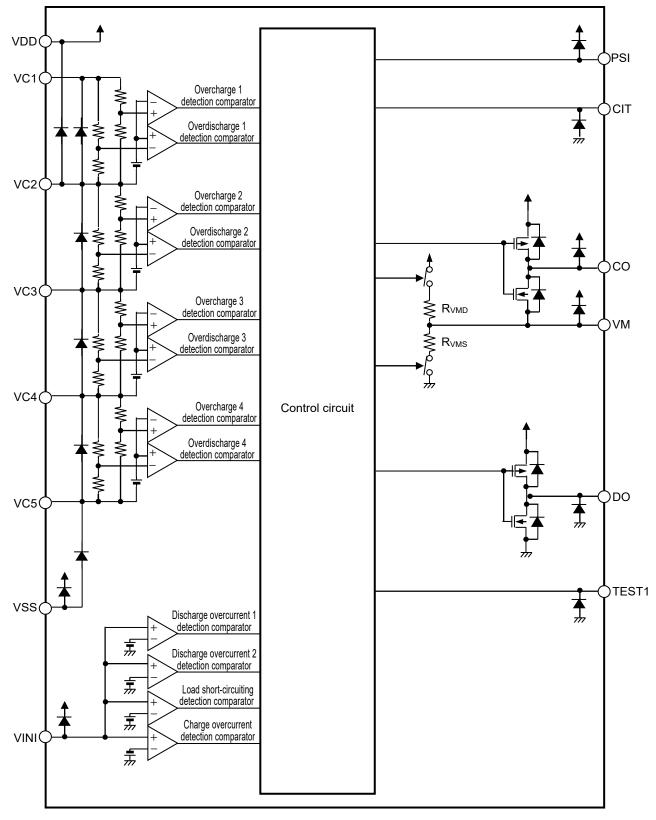
• Lithium-ion rechargeable battery packs

# Package

• 16-Pin TSSOP

# Block Diagram

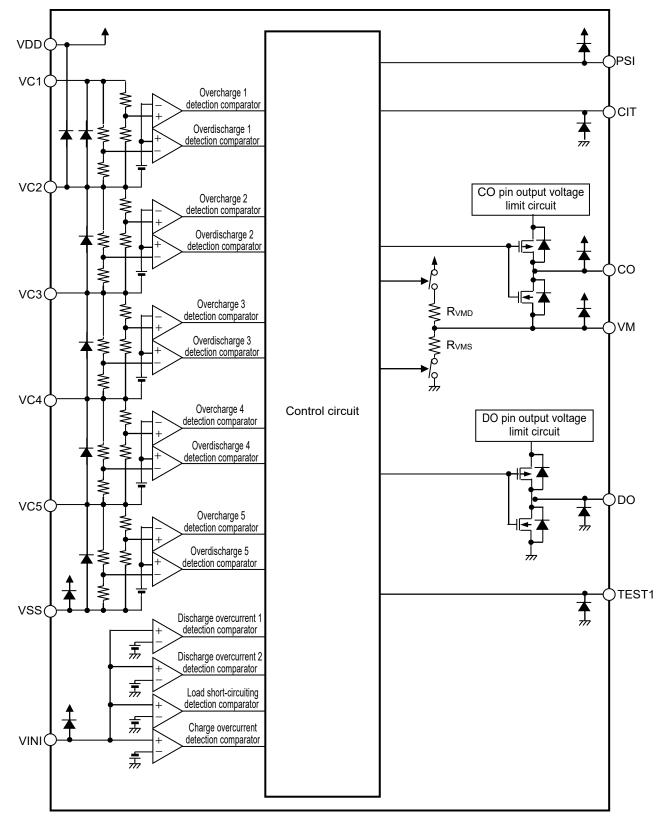
1. S-82B4A Series



**Remark** Diodes in the figure are parasitic diodes.

#### 2. S-82B5A Series

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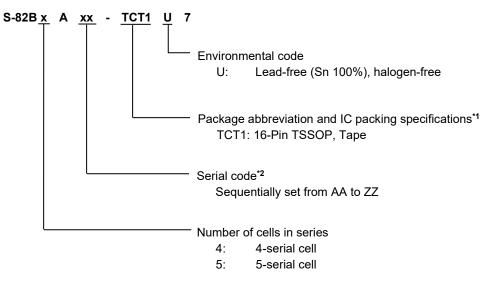


Remark Diodes in the figure are parasitic diodes.

Figure 2

## Product Name Structure

1. Product name



- \*1. Refer to the tape drawing.
- \*2. Refer to "3. Product name list".

#### 2. Package

Table 1	Package Drawing Codes
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Package Name Dimension		Таре	Reel		
16-Pin TSSOP	FT016-A-P-SD	FT016-A-C-SD	FT016-A-R-S1		

#### 3. Product name list

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#### 3.1 S-82B5A Series

	Table 2 (1 / 2)												
Product Name	Overcharge Detection Voltage [Vcu]	Overcharge Release Voltage [V <sub>CL</sub> ]	Overdischarge Detection Voltage [V <sub>DL</sub> ]	Overdischarge Release Voltage [V <sub>DU</sub> ]	Discharge Overcurrent 1 Detection Voltage [V <sub>DIOV1</sub> ]	Discharge Overcurrent 2 Detection Voltage [V <sub>DIOV2</sub> ]	Load Short-circuiting Detection Voltage [V <sub>SHORT</sub> ]	Charge Overcurrent Detection Voltage [Vciov]					
S-82B5AAA-TCT1U7	4.225 V	4.025 V	2.500 V	2.500 V	50 mV	100 mV	400 mV	–50 mV					

#### Table 2 (2 / 2)

Product Name	Delay Time Combination*1	0 V Battery Charge	Power-down Function	Release Condition of Discharge Overcurrent Status <sup>*2</sup>
S-82B5AAA-TCT1U7	(1)	Inhibited	Available	Load disconnection

\*1. Refer to **Table 3** about the details of the delay time combinations.

\*2. Release condition of discharge overcurrent status: Load disconnection, charger connection

Remark Please contact our sales representatives for products other than the above.

		Table 3			
Delay Time	Overcharge Detection	Overdischarge Detection	Discharge Overcurrent 2	Charge Overcurrent	
,	Delay Time Delay Time		Detection Delay Time	Detection Delay Time	
Combination	[tcu]	[t <sub>DL</sub> ]	[tdiov2]	[tciov]	
(1)	1.0 s	128 ms	16 ms	16 ms	

**Remark** The delay times can be changed within the range listed in **Table 4**. For details, please contact our sales representatives.

Table 4									
Delay Time	Symbol		Selection Range				Remark		
Overcharge detection delay time	tcu	256 ms	512 ms	1.0 s	2.0 s	-	-	-	Select a value from the left.
Overdischarge detection delay time	t <sub>DL</sub>	32 ms	64 ms	128 ms	256 ms	512 ms	1.0 s	-	Select a value from the left.
Discharge overcurrent 2 detection delay time	t <sub>DIOV2</sub>	4 ms	8 ms	16 ms	32 ms	64 ms	-	-	Select a value from the left.
Charge overcurrent detection delay time	tciov	4 ms	8 ms	16 ms	32 ms	64 ms	128 ms	256 ms	Select a value from the left.

# Pin Configuration

# 1. 16-Pin TSSOP

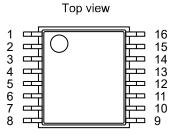


Figure 3

		Table 5
Pin No.	Symbol	Description
1	VC1	Connection pin for battery 1's positive voltage
0	VC2	Connection pin for battery 1's negative voltage,
2	VC2	Connection pin for battery 2's positive voltage
3	VC3	Connection pin for battery 2's negative voltage,
3	VC3	Connection pin for battery 3's positive voltage
4	VC4	Connection pin for battery 3's negative voltage,
4	VC4	Connection pin for battery 4's positive voltage
5	VC5	Connection pin for battery 4's negative voltage,
5	VC5	Connection pin for battery 5's positive voltage
6	VSS	Input pin for negative power supply,
0	V33	Connection pin for battery 5's negative voltage
7	VINI	Voltage detection pin between VSS pin and VINI pin
0	OIT	Capacitor connection pin for discharge overcurrent
8	CIT	1 detection delay time
9	NC <sup>*1</sup>	No connection
10	TEST1*2	Test pin
11	PSI	Control pin for power-saving
40	5.0	Connection pin of discharge control FET gate
12	DO	(CMOS output)
13	NC <sup>*1</sup>	No connection
		Connection pin of charge control FET gate
14	CO	(CMOS output)
15	VM	Voltage detection pin between VSS pin and VM pin
16		Input pin for positive power supply,
16	VDD	Connection pin for battery 1's positive voltage

\*1. The NC pin is electrically open. The NC pin can be connected to the VDD pin or the VSS pin.

\*2. Set the TEST1 pin open in use.

# Absolute Maximum Ratings

Table 6

			(Ta = +25°C unless otherwise sp	ecified)
Item	Symbol	Applied Pin	Absolute Maximum Rating	Unit
Input voltage between VDD pin and VSS pin	V <sub>DS</sub>	VDD	Vss - 0.3 to Vss + 28.0	V
		VC1	$V_{VC2} - 0.3$ to $V_{VC2} + 6.0$	V
Input pin voltage 1	VIN1	VC3	$V_{\text{VC4}}-0.3$ to $V_{\text{DD}}+0.3 \leq V_{\text{VC4}}+6.0$	V
		VC4	$V_{\text{VC5}}-0.3$ to $V_{\text{DD}}+0.3 \leq V_{\text{VC5}}+6.0$	V
Input pin voltage 2	V <sub>IN2</sub>	VC2	$V_{DD}-6.0 \leq V_{VC3}-0.3$ to $V_{DD}+0.3 \leq V_{VC3}+6.0$	V
Input pin voltage 3	V <sub>IN3</sub>	VC5	$V_{\text{SS}} - 0.3$ to $V_{\text{DD}} + 0.3 \leq V_{\text{SS}} + 6.0$	V
Input pin voltage 4	VIN4	TEST1, CIT	Vss – 0.3 to Vss + 6.0	V
Input pin voltage 5	V <sub>IN5</sub>	PSI, VM, VINI	$V_{DD} - 28.0$ to $V_{DD} + 0.3$	V
Output pin voltage 1	Vout1	DO	$V_{\text{SS}} - 0.3$ to $V_{\text{DD}} + 0.3 \leq V_{\text{SS}} + 28.0$	V
Output pin voltage 2	Vout2	СО	$V_{\text{DD}}-28.0 \leq V_{\text{VM}}-0.3$ to $V_{\text{DD}}+0.3$	V
Operation ambient temperature	T <sub>opr</sub>	_	-40 to +85	°C
Storage temperature	T <sub>stg</sub>	_	-55 to +125	°C

# Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

# Thermal Resistance Value

Table 7									
Item	Symbol	Cond	Min.	Тур.	Max.	Unit			
			Board A	_	88	_	°C/W		
		16-Pin TSSOP	Board B	_	74	-	°C/W		
Junction-to-ambient thermal resistance*1	$\theta_{JA}$		Board C	-	_	-	°C/W		
			Board D	_	_		°C/W		
			Board E	_	_	_	°C/W		

\*1. Test environment: compliance with JEDEC STANDARD JESD51-2A

**Remark** Refer to "**■ Power Dissipation**" and "Test Board" for details.

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# Electrical Characteristics

		Table 8 (1 /	2)				
		(V1 = V2 = V3 =	: V4 = V5 = 3.5 V	′, Ta = +25°	C unless otherw	/ise sp	ecified
Item	Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Detection Voltage							
Overcharge detection voltage n	Vcun	_	$V_{\text{CU}}-0.020$	Vcu	$V_{CU} + 0.020$	V	1
Overcharge release voltage n	VcLn	_	$V_{\text{CL}}-0.050$	Vcl	$V_{CL} + 0.050$	V	1
Overdischarge detection voltage n	VDLn	_	$V_{\text{DL}}-0.050$	VDL	V <sub>DL</sub> + 0.050	V	1
Overdischarge release voltage n	V <sub>DUn</sub>	-	V <sub>DU</sub> - 0.100	V <sub>DU</sub>	V <sub>DU</sub> + 0.100	V	1
Discharge overcurrent 1 detection voltage	Vdiov1	-	Vdio1v - 5	VDIOV1	V <sub>DIOV1</sub> + 5	mV	1
Discharge overcurrent 2 detection voltage	Vdiov2	-	V <sub>DIOV2</sub> – 10	V <sub>DIOV2</sub>	V <sub>DIOV2</sub> + 10	mV	1
Load short-circuiting detection voltage	VSHORT	-	Vshort – 20	VSHORT	Vshort + 20	mV	1
Charge overcurrent detection voltage	Vciov	-	Vciov – 5	Vciov	Vciov + 5	mV	1
Delay Time	-						
CIT pin charge current	Ісіт	-	80	120	170	nA	1
CIT pin detection voltage	Vcit	_	1.1	1.2	1.3	V	1
Overcharge detection delay time	<b>t</b> cu	-	$t_{CU}  imes 0.7$	tcu	tcu × 1.3	-	1
Overdischarge detection delay time	tol	-	$t_{\text{DL}}  imes 0.7$	t <sub>DL</sub>	$t_{\text{DL}} \times 1.3$	-	1
Discharge overcurrent 2 detection delay time	tdiov2	-	$t_{\text{DIOV2}} \times 0.7$	tdiov2	$t_{\text{DIOV2}} \times 1.3$	-	1
Load short-circuiting detection delay time	tshort	Internally fixed delay time	100	300	600	μs	1
Charge overcurrent detection delay time	tciov	-	$t_{CIOV}  imes 0.7$	tciov	tciov × 1.3	-	1
PSI pin response time	tpsi	-	1.4	2.0	2.6	ms	1
0 V Battery Charge							
0 V battery charge starting charger voltage	V0CHA	0 V battery charge enabled	-	0.8	1.5	V	1
0 V battery charge inhibition battery voltage n	Voinh	0 V battery charge inhibited	1.0	1.2	1.5	v	1

**Remark** n = 1, 2, 3, 4, 5

# BATTERY PROTECTION IC FOR 4-SERIAL OR 5-SERIAL-CELL PACK S-82B4A/5A Series

		<b>Table 8 (2 / 2)</b> (V1 = V2 = V3 = V4 = V5 = 3	.5 V, Ta =	+25°C unles	ss otherw	ise sp	pecified)
ltem	Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Internal Resistance							
Resistance between VDD pin and VM pin	1	-	0.5	1	1.5	MΩ	1
Resistance between VM pin and VSS pin	Rvms	_	7.5	15	30	kΩ	1
Input Voltage	1	1 1				-	
Operation voltage between VDD pin and	VDSOP	Fixed output voltage of DO	5.0		24.0	v	1
VSS pin	VDSOP	pin and CO pin	5.0	_	24.0	v	1
External control input pin							
PSI pin reverse voltage "H"	VPSIH	-	0.8	1.0	1.3	V	1
PSI pin reverse voltage "L"	VPSIL	—	0.5	0.8	1.0	V	1
Input Current							
Current consumption during operation	IOPE	_	_	4	8	μΑ	1
Current consumption during power-down	IPDN	_	-	_	0.1	μA	1
Current consumption during power-saving	IPSV	_	_	-	0.1	μA	1
VC1 pin current	Ivc1	_	_	0.25	0.4	μA	1
VC2 pin current	Ivc2	-	-0.4	0.05	0.4	μA	1
VC3 pin current	Ілсз	-	-0.4	-0.1	0.4	μΑ	1
VC4 pin current	Ivc4	-	-0.4	-0.1	0.4	μA	1
VC5 pin current	Ivc5	-	-0.4	-0.1	0.4	μA	1
PSI pin current "H"	IPSIH	-	-400	-200	-100	nA	1
PSI pin current "L"	I <sub>PSIL</sub>	-	100	200	400	nA	1
Output pin							
CO pin voltage "H"	Vсон	4-serial cell	-	_	Vdd	V	1
	VCON	5-serial cell	-	$V_{VC2}-0.5$	V <sub>VC2</sub>	V	1
DO pin voltage "H"	Vdoh	4-serial cell	_	-	Vdd	V	1
	• DOIN	5-serial cell	_	$V_{VC2}-0.5$	V <sub>VC2</sub>	V	1
CO pin source current	Ісон	-	10	_	-	μΑ	1
CO pin sink current	Icol	-	180	200	-	μΑ	1
DO pin source current	Ідон	-	10	-	-	μΑ	1
DO pin sink current	IDOL	-	1700	2000	-	μΑ	1

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### Test Circuits

- Caution Unless otherwise specified, the output voltage levels "H" and "L" at CO pin (V<sub>CO</sub>) and DO pin (V<sub>DO</sub>) are judged as follows.
  - L:  $[V_{CO}, V_{DO}] \leq V_{DS} \times 0.1 V$
  - H: [Vco, VDo] > VDS × 0.1 V



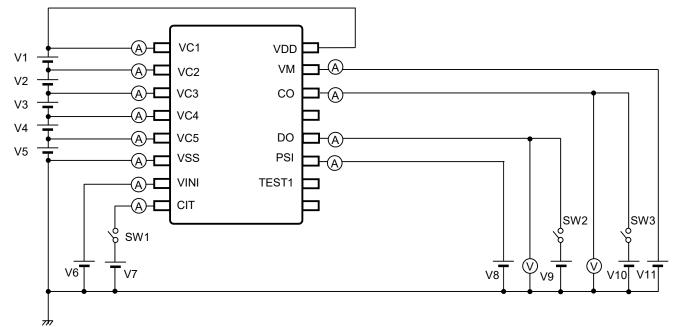


Figure 4 Test circuit 1

This section provides explanations of Test items using Test circuit 1. Perform each test after setting as shown in **Table 9**.

Table 9	Initial Setting	of Test	Circuit 1	(1 / 2)	
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Symbol	V1	V2	V3	V4	V5	V6	V7	V8	V9	V10	V11	SW1	SW2	SW3
Setting	3.5 V	0 V	0 V	Vds	_	_	0 V	ON	OFF	OFF				

#### 1. Overcharge detection voltage n (Vcun), overcharge release voltage n (VcLn)

Overcharge detection voltage 1 (V<sub>CU1</sub>) is defined as the voltage V1 at which V<sub>CO</sub> goes from "H" to "L" when the voltage V1 is gradually increased after setting V1 = V2 = V3 = V4 = V5 = V<sub>CUn</sub> – 0.05 V. Overcharge release voltage 1 (V<sub>CL1</sub>) is defined as the voltage V1 at which V<sub>CO</sub> goes from "L" to "H" when the voltage V1 is then gradually decreased after setting V2 = V3 = V4 = V5 = V<sub>CLn</sub> – 0.05 V, V11 = 0.2 V.

Overcharge detection voltage n ( $V_{CUn}$ ) and overcharge release voltage n ( $V_{CLn}$ ) (n = 2 to 5) can be determined in the same way as when n = 1.

#### 2. Overdischarge detection voltage n (V<sub>DLn</sub>), overdischarge release voltage n (V<sub>DUn</sub>)

Overdischarge detection voltage 1 (V<sub>DL1</sub>) is defined as the voltage V1 at which V<sub>D0</sub> goes from "H" to "L" when the voltage V1 is gradually decreased. Overdischarge release voltage 1 (V<sub>DU1</sub>) is defined as the voltage V1 at which V<sub>D0</sub> goes from "L" to "H" when the voltage V1 is then gradually increased after setting V11 = 0.2 V. Overdischarge detection voltage n (V<sub>DLn</sub>) and overdischarge release voltage n (V<sub>DUn</sub>) (n = 2 to 5) can be determined in the same way as when n = 1.

#### 3. Discharge overcurrent 1 detection voltage (VDIOV1)

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Discharge overcurrent 1 detection voltage ( $V_{DIOV1}$ ) is defined as the voltage V6 at which CIT pin current changes from the direction of flowing into the IC to the direction of flowing out from the IC when the voltage V6 is gradually increased after setting V7 = 0.01 V.

#### 4. Discharge overcurrent 2 detection voltage (VDIOV2)

Discharge overcurrent 2 detection voltage ( $V_{DIOV2}$ ) is defined as the voltage V6 at which  $V_{DO}$  goes from "H" to "L" when the voltage V6 is gradually increased after setting V11 = 0.5 V.

#### 5. Load short-circuiting detection voltage (VSHORT)

Load short-circuiting detection voltage ( $V_{SHORT}$ ) is defined as the voltage V6 at which delay time from when V6 is increased after setting V11 = 0.5 V to when  $V_{DO}$  goes from "H" to "L" is load short-circuiting detection delay time ( $t_{SHORT}$ ).

#### 6. Charge overcurrent detection voltage (VCIOV)

Charge overcurrent detection voltage ( $V_{CIOV}$ ) is defined as the voltage V6 at which  $V_{CO}$  goes from "H" to "L" when the voltage V6 is gradually decreased after setting V11 = -0.1 V.

#### 7. CIT pin charge current (ICIT), CIT pin detection voltage (VCIT)

CIT pin charge current ( $I_{CIT}$ ) is defined as the CIT pin current when setting V6 = ( $V_{DIOV1} + V_{DIOV2}$ ) / 2. CIT pin detection voltage ( $V_{CIT}$ ) is defined as the voltage V7 at which  $V_{DO}$  goes from "H" to "L" when the voltage V7 is then gradually increased.

#### 8. Overcharge detection delay time (tcu)

Overcharge detection delay time (t<sub>CU</sub>) is the time period from when the voltage V1 exceeds  $V_{CU1}$  after setting V1 = V2 = V3 = V4 = V5 = 3.5 V till when  $V_{CO}$  goes from "H" to "L".

#### 9. Overdischarge detection delay time (t<sub>DL</sub>)

Overdischarge detection delay time ( $t_{DL}$ ) is the time period from when the voltage V1 falls below V<sub>DL1</sub> after setting V1 = V2 = V3 = V4 = V5 = 3.5 V till when V<sub>D0</sub> goes from "H" to "L".

#### 10. Discharge overcurrent 2 detection delay time (tDIOV2)

Discharge overcurrent 2 detection delay time ( $t_{DIOV2}$ ) is the time period from when the voltage V6 exceeds  $V_{DIOV2}$  after setting V11 = 0.5 V till when V<sub>DO</sub> changes from "H" to "L".

#### 11. Load short-circuiting detection delay time (tshort)

Load short-circuiting detection delay time ( $t_{SHORT}$ ) is the time period from when the voltage V6 exceeds V<sub>SHORT</sub> after setting V11 = 0.5 V till when V<sub>DO</sub> changes from "H" to "L".

#### 12. Charge overcurrent detection delay time (tciov)

Charge overcurrent detection delay time ( $t_{CIOV}$ ) is the time period from when the voltage V6 falls below  $V_{CIOV}$  after setting V11 = -0.1 V till when  $V_{CO}$  changes from "H" to "L".

#### 13. PSI pin response time (t<sub>PSI</sub>)

PSI pin response time ( $t_{PSI}$ ) is the time period from when the voltage V8 is changed to 0 V till when V<sub>DO</sub> changes from "H" to "L".

#### 14. 0 V battery charge starting charger voltage (V<sub>0CHA</sub>) (0 V battery charge enabled)

This IC reaches the overdischarge status after setting V1 =  $V_{DL1} - 0.1$  V. Then set V1 = V2 = V3 = V4 = V5 = 0 V. 0 V battery charge starting charger voltage (V<sub>0CHA</sub>) is defined as the absolute value of voltage V11 at which I<sub>C0</sub> exceeds 1.0  $\mu$ A when the voltage V11 is then gradually decreased after setting SW3 ON and V10 = V11 = -0.5 V.

#### 15. 0 V battery charge inhibition battery voltage n (VOINHn) (0 V battery charge inhibited)

0 V battery charge inhibition battery voltage 1 ( $V_{0INH1}$ ) is defined as the voltage V1 at which V<sub>CO</sub> goes from "H" to "L" when the voltage V1 is gradually decreased after setting V1 = V2 = V3 = V4 = V5 = V<sub>DLn</sub> - 0.1 V. 0 V battery charge inhibition battery voltage n ( $V_{0INHn}$ ) (n = 2 to 5) can be determined in the same way as when n = 1.

#### 16. Resistance between VM pin and VDD pin (RVMD)

Resistance between VM pin and VDD pin ( $R_{VMD}$ ) is defined by  $R_{VMD} = (V_{DS} + 0.1) / I_{VM}$  using  $I_{VM}$  when setting V1 = V2 = V3 = V4 = V5 = 1.5 V and V11= -0.1 V.

#### 17. Resistance between VM pin and VSS pin (R<sub>VMS</sub>)

Resistance between VM pin and VSS pin ( $R_{VMS}$ ) is defined by  $R_{VMS}$  = V11 /  $I_{VM}$  using  $I_{VM}$  when setting V6 = 1.0 V and V11 = 2.0 V.

#### 18. PSI pin reverse voltage "H" (VPSIH)

PSI pin reverse voltage "H" ( $V_{PSIH}$ ) is defined as the voltage V8 at which  $V_{DO}$  goes from "L" to "H" when the voltage V8 is gradually increased after setting V8 = 0 V.

#### 19. PSI pin reverse voltage "L" (VPSIL)

PSI pin reverse voltage "L" ( $V_{PSIL}$ ) is defined as the voltage V8 at which  $V_{DO}$  goes from "H" to "L" when the voltage V8 is gradually decreased.

#### 20. Current consumption during operation (IOPE)

Current consumption during operation (IOPE) is defined as the sum of VSS pin current, VM pin current and VINI pin current after setting SW1 OFF.

#### 21. Current consumption during power-down (IPDN)

Current consumption during power-down (IPDN) is defined as IVss under the setting conditions of V1 = V2 = V3 = V4 = V5 = 1.5 V and V11 = V<sub>DS</sub>.

#### 22. Current consumption during power-saving (IPSV)

Current consumption during power-saving ( $I_{PSV}$ ) is defined as  $I_{VSS}$  under the setting conditions of V8 = 0 V and V11 =  $V_{DS}$ .

#### 23. PSI pin current "H" (IPSIH), PSI pin current "L" (IPSIL)

PSI pin current "H" ( $I_{PSIH}$ ) is defined as  $I_{PSI}$  when setting V8 = V<sub>DS</sub> - 1 V after setting V8 = V<sub>DS</sub>. PSI pin current "L" ( $I_{PSIL}$ ) is defined as  $I_{PSI}$  when setting V8 = ( $V_{PSIH} + V_{PSIL}$ ) / 2 after setting V8 = 0 V.

#### 24. CO pin voltage "H" (Vсон), CO pin source current (Ісон)

CO pin voltage "H" (V<sub>COH</sub>) is defined as CO pin voltage (V<sub>CO</sub>) in the settings shown in **Table 9**. CO pin source current (I<sub>COH</sub>) is defined as I<sub>CO</sub> when setting V10 = V<sub>COH</sub> – 0.5 V and SW3 ON.

#### 25. CO pin sink current (IcoL)

CO pin sink current ( $I_{COL}$ ) is defined as  $I_{CO}$  when setting V1 =  $V_{CU1}$  + 0.1 V, V10 = 0.5 V and SW3 ON.

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### 26. DO pin voltage "H" (VDOH), DO pin source current (IDOH)

DO pin voltage "H" ( $V_{DOH}$ ) is defined as DO pin voltage ( $V_{DO}$ ) in the settings shown in **Table 9**. DO pin source current ( $I_{DOH}$ ) is defined as  $I_{DO}$  when setting V9 =  $V_{DOH} - 0.5$  V and SW2 ON.

#### 27. DO pin sink current (IDOL)

DO pin sink current ( $I_{DOL}$ ) is defined as  $I_{DO}$  when setting V1 =  $V_{DL1} - 0.1$  V, V9 = 0.5 V and SW2 ON.

# Operation

**Remark** Refer to "**Battery Protection IC Connection Example**".

#### 1. Normal status

The status when the CO pin output voltage ( $V_{CO}$ ) = "H" and DO pin output voltage ( $V_{DO}$ ) = "H" is the normal status. CO pin voltage "H" ( $V_{COH}$ ) is the voltage  $V_{CO}$  when the  $V_{CO}$  is "H". DO pin voltage "H" ( $V_{DOH}$ ) is the voltage  $V_{DO}$  when the  $V_{DO}$  is "H".

All the conditions mentioned below should be satisfied for returning to the normal status.

- The voltage of each of the batteries is in the range from the overcharge detection voltage n (V<sub>CUn</sub>) to overdischarge detection voltage n (V<sub>DLn</sub>).
- The VINI pin voltage is in the range of the charge overcurrent detection voltage (V<sub>CIOV</sub>) to discharge overcurrent 1 detection voltage (V<sub>DIOV1</sub>).
- The PSI pin voltage is higher than the PSI pin reverse voltage "H" (VPSIH).
- Caution After a battery is connected, there may be cases when discharging cannot be performed. In this case, this IC returns to the normal status when any of the following conditions is satisfied.
  - (1) Connecting a charger
  - (2) Shorting between the VM pin and the VSS pin
  - (3) Changing the PSI pin voltage to be  $V_{DS} \rightarrow 0 \; V \rightarrow V_{DS}$

#### 2. Overcharge status

When the voltage of any of the batteries exceeds the overcharge detection voltage n ( $V_{CUn}$ ) and the status continues for the overcharge detection delay time ( $t_{CU}$ )<sup>\*1</sup> or longer, the CO pin changes to VM pin voltage. This is the overcharge status. In this case, the charge control FET is turned off and charging is stopped.

The overcharge status is released if either condition mentioned below is satisfied.

- (1)  $V_{\text{VM}} < 0.3$  V typ., and voltage of all batteries  $\leq V_{\text{CLn}}$
- (2)  $V_{\text{VM}} \geq 0.3$  V typ., and voltage of all batteries  $\leq V_{\text{CUn}}$

\*1. Refer to "6. Delay time setting" for details.

Remark	V <sub>VM</sub> :	VM pin voltage
	V <sub>CUn</sub> :	Overcharge detection voltage n (n = 1, 2, 3, 4, 5)
	V <sub>CLn</sub> :	Overcharge release voltage n (n = 1, 2, 3, 4, 5)

#### 3. Overdischarge status

When the voltage of any of the batteries decreases to the overdischarge detection voltage n ( $V_{DLn}$ ) or lower and the status continues for the overdischarge detection delay time ( $t_{DL}$ )<sup>\*1</sup> or longer, the DO pin changes to the V<sub>SS</sub> level. This is the overdischarge status. The discharge control FET is turned off and discharging is stopped.

The overdischarge status is released if either condition mentioned below is satisfied.

- (1)  $V_{\text{VM}} \leq 0~V$  typ., and voltage of all batteries  $\geq V_{DLn}$
- (2)  $V_{VM} > 0$  V typ., and voltage of all battery  $\ge V_{DUn}$

#### \*1. Refer to "6. Delay time setting" for details.

Remark $V_{VM}$ :VM pin voltage $V_{DLn}$ :Overdischarge detection voltage n (n = 1, 2, 3, 4, 5) $V_{DUn}$ :Overdischarge release voltage n (n = 1, 2, 3, 4, 5)

#### 3.1 With power-down function

When this IC reaches the overdischarge status, the VM pin is pulled up to the  $V_{DD}$  level by a resistance between VM pin and VDD pin ( $R_{VMD}$ ). If the VM pin voltage changes to 0.7 V typ. or higher, the power-down function starts to operate and most operations in this IC halt. The CO pin changes to VM pin voltage. In this case, the charge control FET is turned off and charging is stopped.

By connecting a battery charger, the power-down function is released when the VM pin voltage is 0.7 V typ. or lower.

#### 4. Discharge overcurrent status

When the discharge current increases to a certain value or more, the VINI pin voltage increases to the level of discharge overcurrent 1 detection voltage (VDIOV1) or higher. If the condition continues for the discharge overcurrent 1 detection delay time (tDIOV1)\*1 or longer, the DO pin changes to the Vss level. This is the discharge overcurrent status. The discharge control FET is turned off and discharging is stopped.

Discharge overcurrent is detected at the following three levels: VDIOV1, VDIOV2, and VSHORT. When discharge overcurrent 2 detection voltage (VDIOV2) and load short-circuiting detection voltage (VSHORT) are detected, the same operations as VDIOV1 detection are performed.

#### 4.1 Release condition of discharge overcurrent status "Load disconnection"

Under the discharge overcurrent status, VM pin and VSS pin are shorted by  $R_{VMS}$  in this IC. However, the VM pin voltage is the  $V_{DD}$  level due to the load as long as the load is connected. When the load is disconnected, the VM pin voltage returns to the Vss level. When the VM pin voltage returns to  $V_{DS}/3$  or lower, this IC releases the discharge overcurrent status.

 $R_{\text{VMD}}$  is not connected in the discharge overcurrent status.

#### 4.2 Release condition of discharge overcurrent status "Charger connection"

Under the discharge overcurrent status, VDD pin and VM pin are shorted by  $R_{VMD}$  in this IC. When a battery is connected to a charger and VM pin voltage returns to  $V_{DIOV1}$  or lower, this IC releases the discharge overcurrent status.

RVMs is not connected in the discharge overcurrent status.

#### 5. Charge overcurrent status

When the charge current increases to a certain value or more, the VINI pin voltage decreases to the level of charge overcurrent detection voltage (VCIOV) or lower. If the status continues for the charge overcurrent detection delay time (tCIOV)<sup>\*1</sup> or longer, the CO pin voltage changes to the VM pin voltage. This is the charge overcurrent status. In this case, the charge control FET is turned off and charging is stopped. The VM pin is pulled up to the V<sub>DD</sub> level by a resistance between VM pin and VDD pin (R<sub>VMD</sub>).

The charge overcurrent status is released if the VM pin voltage increases 0.3 V typ. or higher.

\*1. Refer to "6. Delay time setting" for details.

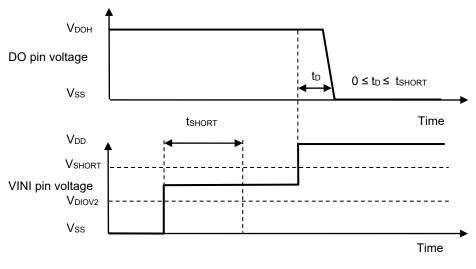
#### 6. Delay time setting

Users are able to set delay time for the period from when this IC detects change in the voltage of any of the batteries or the VINI pin until when it outputs to the CO pin or DO pin. The discharge overcurrent 1 detection delay time ( $t_{DIOV1}$ ) is determined by constant current in this IC and an external capacitor. The other detection delay times are fixed internally.

#### 6.1 Other than discharge overcurrent 1 detection delay time (t<sub>DIOV1</sub>)

The detection delay times are determined by dividing a clock of approximately 4 kHz by the counter.

**Remark**  $t_{DIOV2}$  and  $t_{SHORT}$  start when  $V_{DIOV2}$  is detected. When  $V_{SHORT}$  is detected over  $t_{SHORT}$  after the detection of  $V_{DIOV2}$ , this IC turns the discharge control FET off within  $t_{DIOV2}$  or  $t_{SHORT}$  of each detection.





#### 6. 2 Discharge overcurrent 1 detection delay time (tDIOV1)

In the discharge overcurrent 1 detection, when the VINI pin voltage increases to discharge overcurrent 1 detection voltage ( $V_{DIOV1}$ ) or higher, the internal circuit of this IC starts charging to an external capacitor connected to the CIT pin via the CIT pin current ( $I_{CIT}$ ) = 120 nA typ. When the CIT pin voltage increases to the CIT pin detection voltage ( $V_{CIT}$ ) or higher, the DO pin voltage changes to Vss level. This period is discharge overcurrent 1 detection delay time ( $t_{DIOV1}$ ).

 $t_{DIOV1}$  is calculated by the following formula.  $t_{DIOV1}$  [s] = C<sub>CIT</sub> [F] × V<sub>CIT</sub> [V] / I<sub>CIT</sub> [A]

If  $C_{CIT}$  = 0.01  $\mu$ F, t<sub>DIOV1</sub> is calculated as follows: t<sub>DIOV1</sub> [s] = 0.01  $\mu$ F × 1.2 V typ. / 120 nA typ. = 100 ms typ.

#### 7. 0 V Battery charge function

Regarding how to charge a self-discharged battery (0 V battery), users are able to select either function mentioned below.

(1) 0 V battery charge enabled

A 0 V battery is charged when charger voltage is higher than the 0 V battery charge starting charger voltage ( $V_{0CHA}$ ).

(2) 0 V battery charge inhibited A 0 V battery is not charged when the voltage of any of the batteries is the 0 V battery charge inhibition battery voltage n (V<sub>0INHn</sub>) or lower.

Caution When the VDD pin voltage is lower than the minimum value of operation voltage between the VDD pin and VSS pin (VDSOP), this IC's operation is not assured.

**Remark** n = 1, 2, 3, 4, 5

#### 8. PSI pin

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When the PSI pin is activated, the power-saving function starts to operate, and most operations halt. In this case, the CO pin changes to the VM pin level, and DO pin changes to the Vss level.

#### Table 10 Status Set by PSI Pin

PSI pin	CO pin	DO pin		
V <sub>PSIH</sub> ≤ PSI pin voltage ≤ V <sub>DD</sub> level	"H"	"H"		
V <sub>PSIL</sub> < PSI pin voltage < V <sub>PSIH</sub>	Maintains the status	Maintains the status		
V <sub>SS</sub> level ≤ PSI pin voltage ≤ V <sub>PSIL</sub>	VM pin level	Vss level		

This IC is initialized and becomes the normal status by deactivating the PSI pin after activating PSI pin and enabling the power-saving function. As a result, each detection operation is carried out after returning to the normal status.

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# Timing Charts

1. Overcharge detection, overdischarge detection

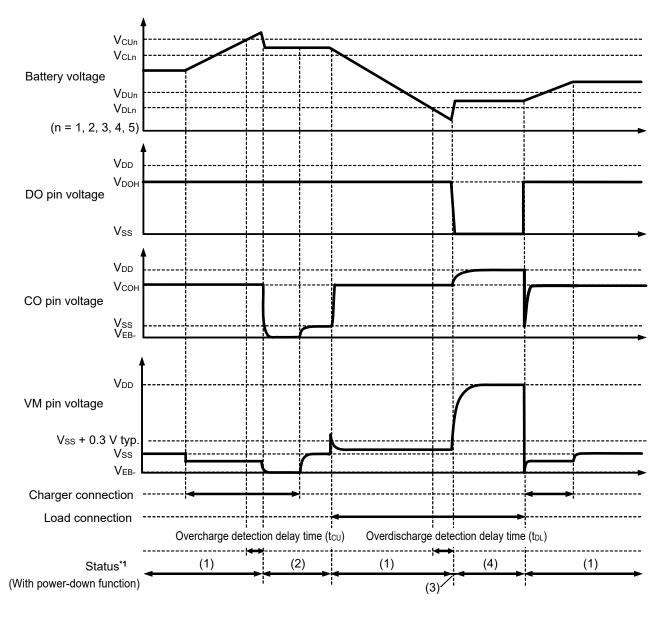


Figure 6

\*1. (1): Normal status

- (2) : Overcharge status
- (3): Overdischarge status
- (4) : Power-down status

#### 2. Discharge overcurrent detection

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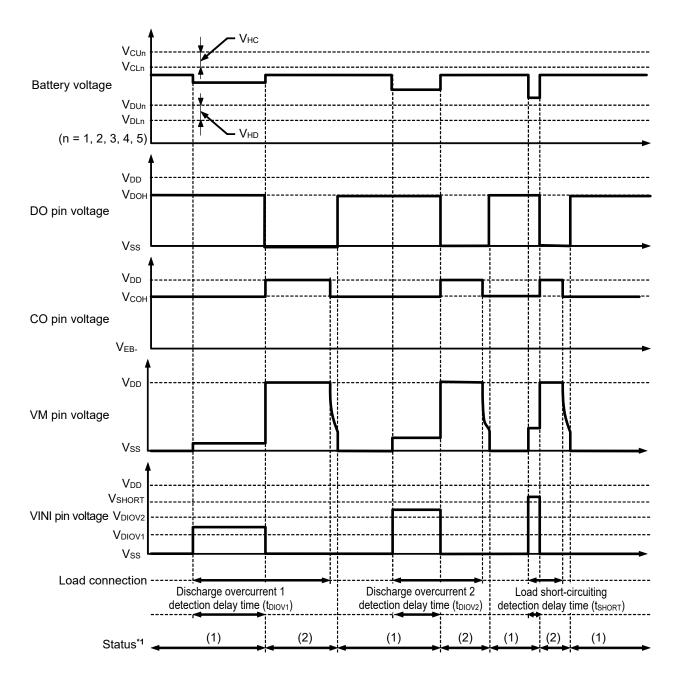


Figure 7

\*1. (1): Normal status

(2) : Discharge overcurrent status

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#### 3. Charge overcurrent detection

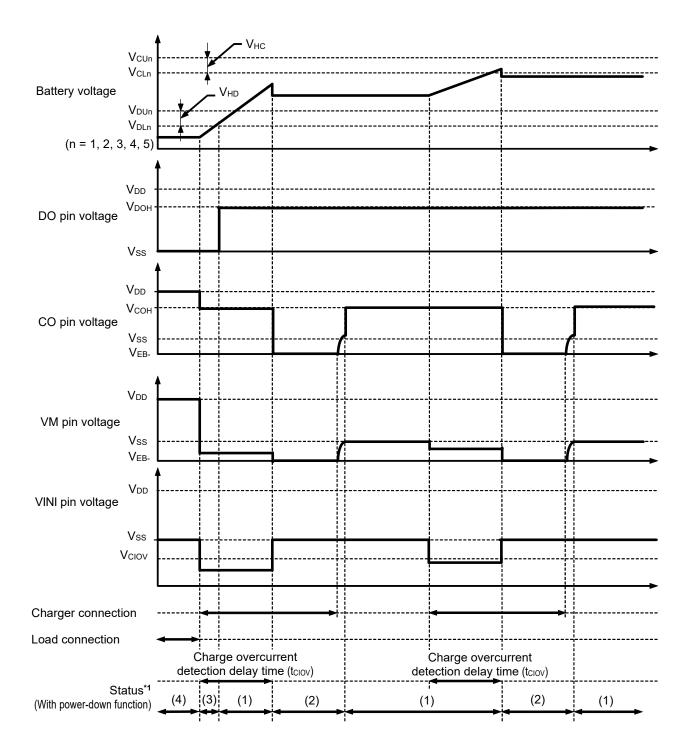


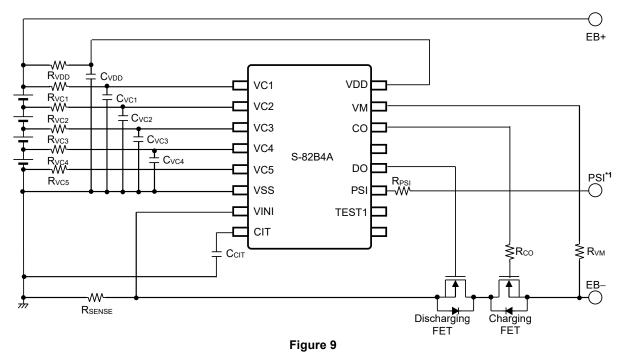
Figure 8

- \*1. (1): Normal status
  - (2) : Charge overcurrent status
  - (3) : Overdischarge status
  - (4) : Power-down status

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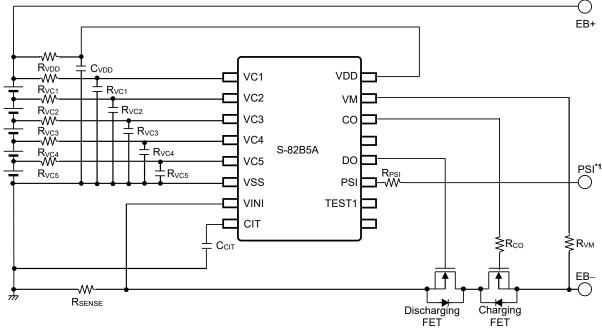
# Connection Examples of Battery Protection IC

# 1. S-82B4A Series (4-serial cell)



\*1. If you do not use the power-saving function, connect the PSI pin to the VDD pin.

**Remark** Regarding the recommended values for external components, refer to "**Table 11 Constants for External Components**".



#### 2. S-82B5A Series (5-serial cell)

Figure 10

- \*1. If you do not use the power-saving function, connect the PSI pin to the VDD pin.
- **Remark** Regarding the recommended values for external components, refer to "**Table 11 Constants for External Components**".

Symbol	Тур.	Unit
Rvdd	100	Ω
R <sub>VCn</sub> (n = 1, 2, 3, 4, 5)	1	kΩ
R <sub>PSI</sub>	1	kΩ
R <sub>co</sub>	1	kΩ
R <sub>VM</sub>	1	kΩ
R <sub>SENSE</sub>	-	mΩ
CVDD	1	μF
C <sub>VCn</sub> (n = 1, 2, 3, 4, 5)	0.1	μF
Ссіт	0.01 or more	μF

#### Table 11 Constants for External Components

Caution 1. The constants may be changed without notice.

- 2. Sufficient evaluation of transient power supply fluctuation and overcurrent protection function with the actual application is needed to determine the proper constants when setting the filter constants between the VDD pin and VSS pin. Contact our sales representatives if setting the constants between the VDD pin and VSS pin to anything other than the recommended values.
- 3. It has not been confirmed whether the operation is normal or not in circuits other than the connection examples. In addition, the connection examples and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.

# Precautions

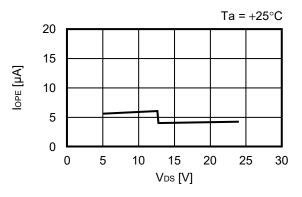
- The application conditions for the input voltage, output voltage, and load current should not exceed the power dissipation.
- Batteries can be connected in any order; however, there may be cases when discharging cannot be performed after a battery is connected. In this case, this IC returns to the normal status when any of the following conditions is satisfied.
  - (1) Connecting a charger
  - (2) Shorting between the VM pin and the VSS pin
  - (3) Changing the PSI pin voltage to be  $V_{DS}\,\rightarrow\,0$  V  $\,\rightarrow\,$   $V_{DS}$
- If an overcharged battery and an overdischarged battery intermix, this IC will change to the overcharge and overdischarge statuses. Therefore, in this case, both charging and discharging are impossible.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- ABLIC Inc. claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

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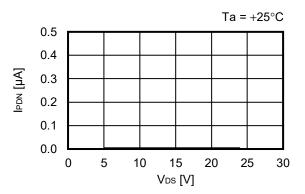
# Characteristics (Typical Data)

### 1. Current consumption

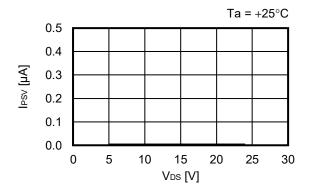
1.1 IOPE VS. VDS



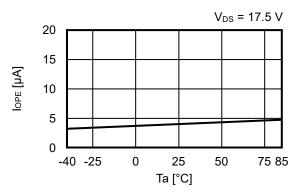
1.3 IPDN VS. VDS



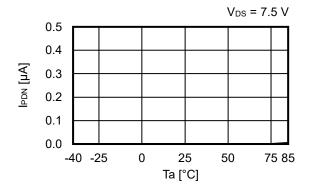
1.5 IPSV VS. VDS

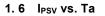


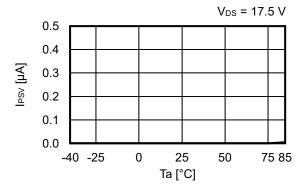
1.2 IOPE vs. Ta

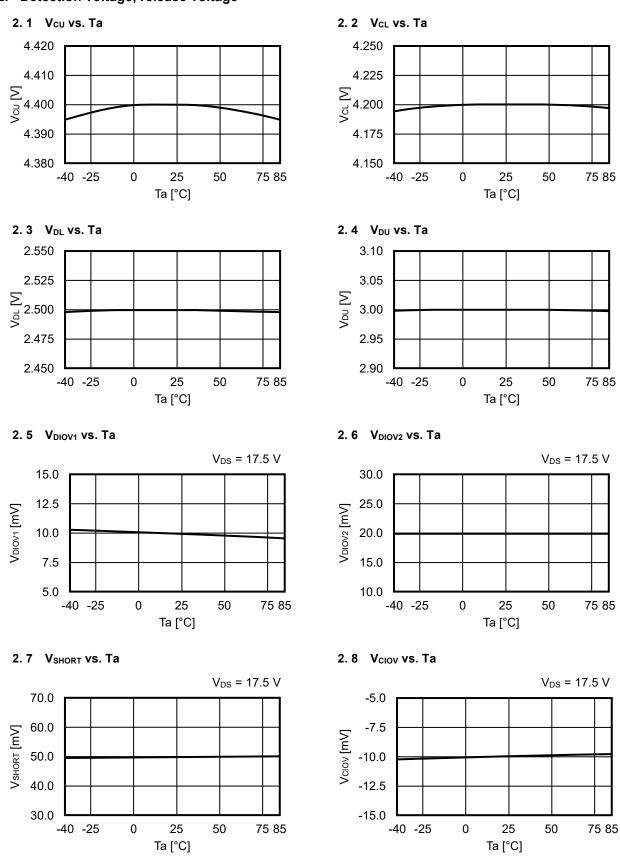


1.4 IPDN vs. Ta







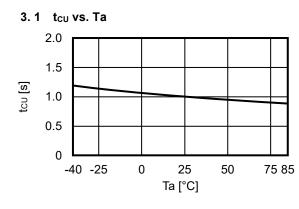


#### 2. Detection voltage, release voltage

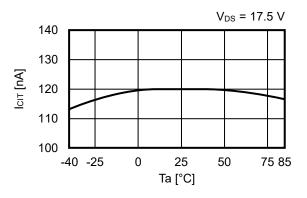
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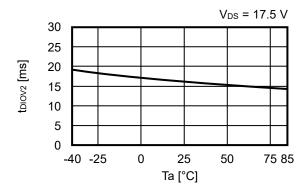
#### 3. Delay time function



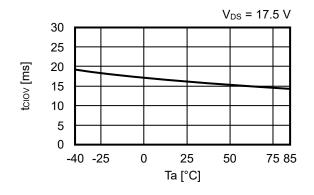


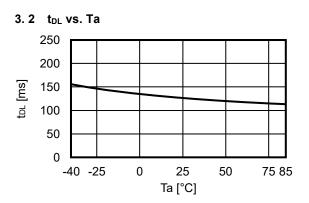


3.5 t<sub>DIOV2</sub> vs. Ta

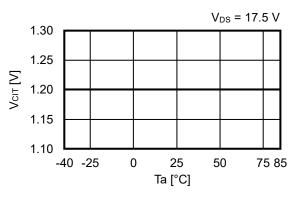


3.7 tciov vs. Ta

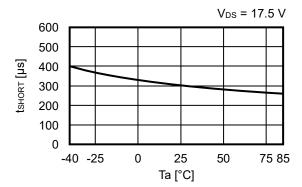






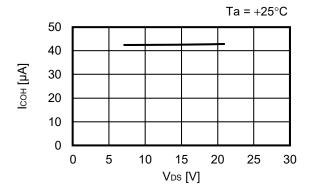






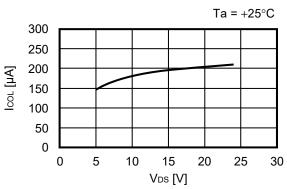
#### 4. Output pin

#### 4.1 ICOH VS. VDS

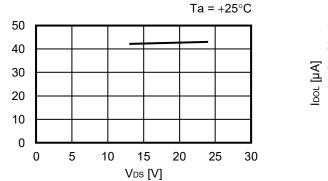


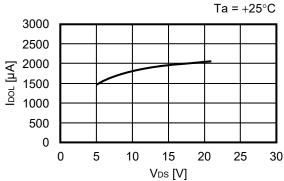
4.3 IDOH VS. VDS

Iрон [µA]





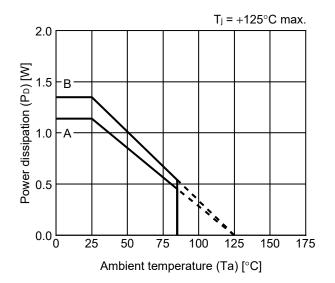




4.2 ICOL VS. VDS

# Power Dissipation

#### 16-Pin TSSOP

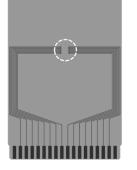


Board	Power Dissipation (P <sub>D</sub> )
А	1.14 W
В	1.35 W
С	_
D	_
E	—

# **16-Pin TSSOP** Test Board

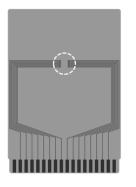
# (1) Board A

) IC Mount Area



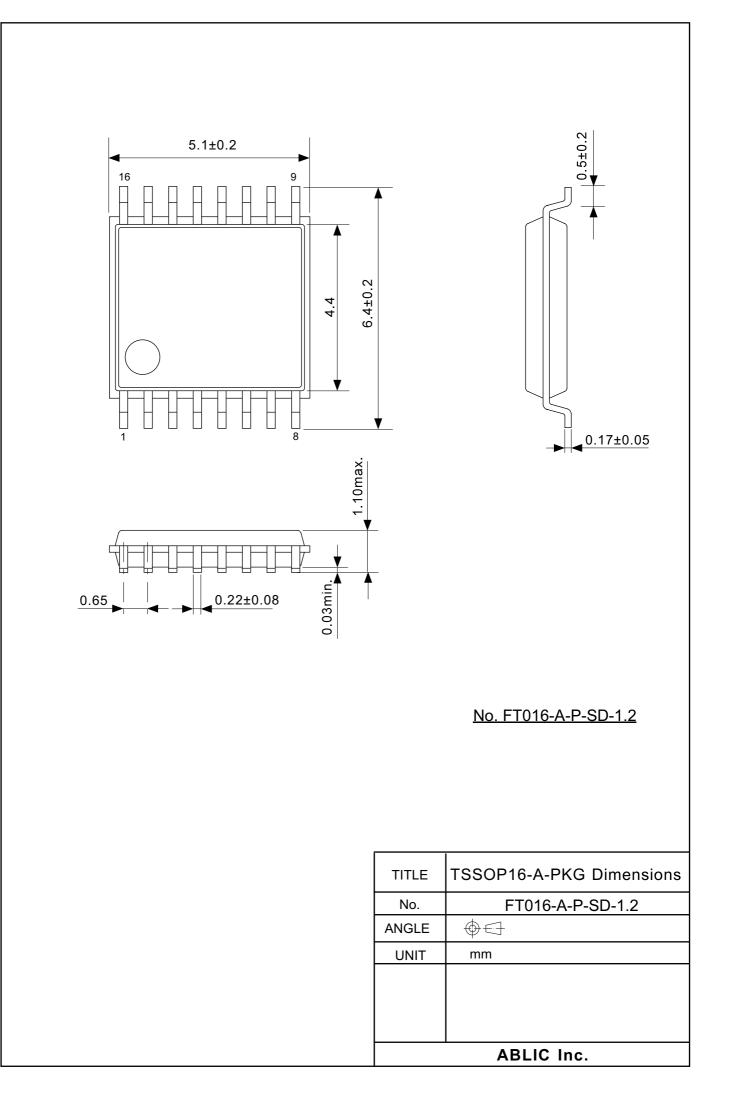
Item		Specification		
Size [mm]		114.3 x 76.2 x t1.6		
Material		FR-4		
Number of copper foil la	ayer	2		
	1	Land pattern and wiring for testing: t0.070		
Copper foil laver [mm]	2	-		
Copper foil layer [mm]	3	-		
	4	74.2 x 74.2 x t0.070		
Thermal via		-		

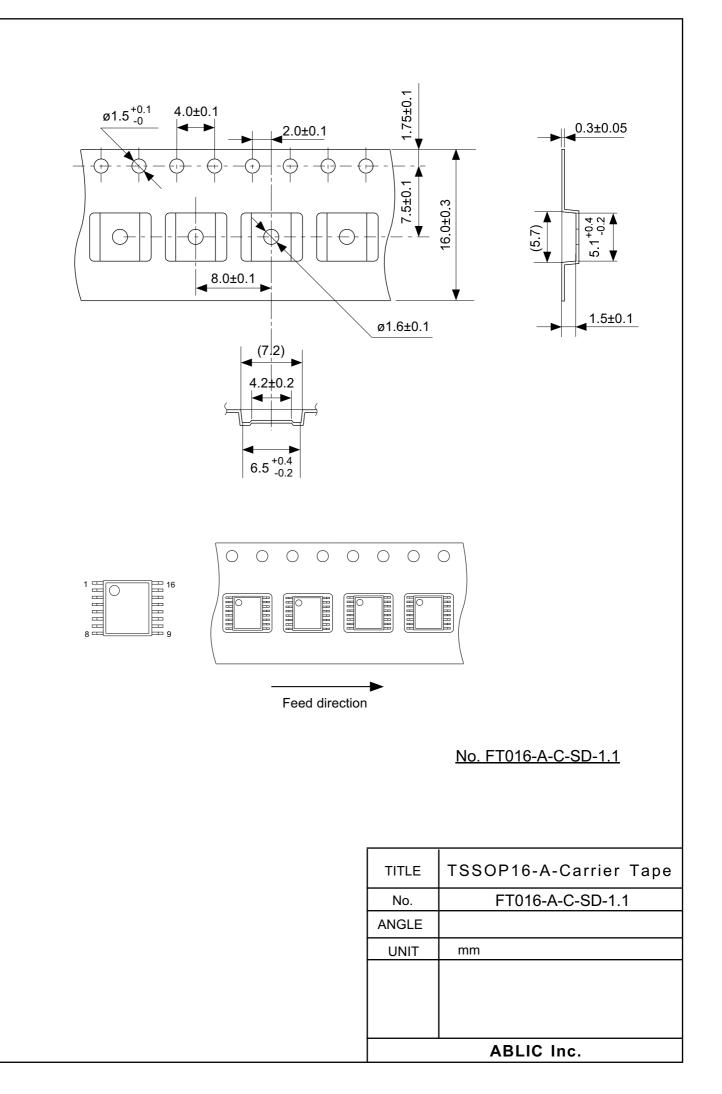
# (2) Board B

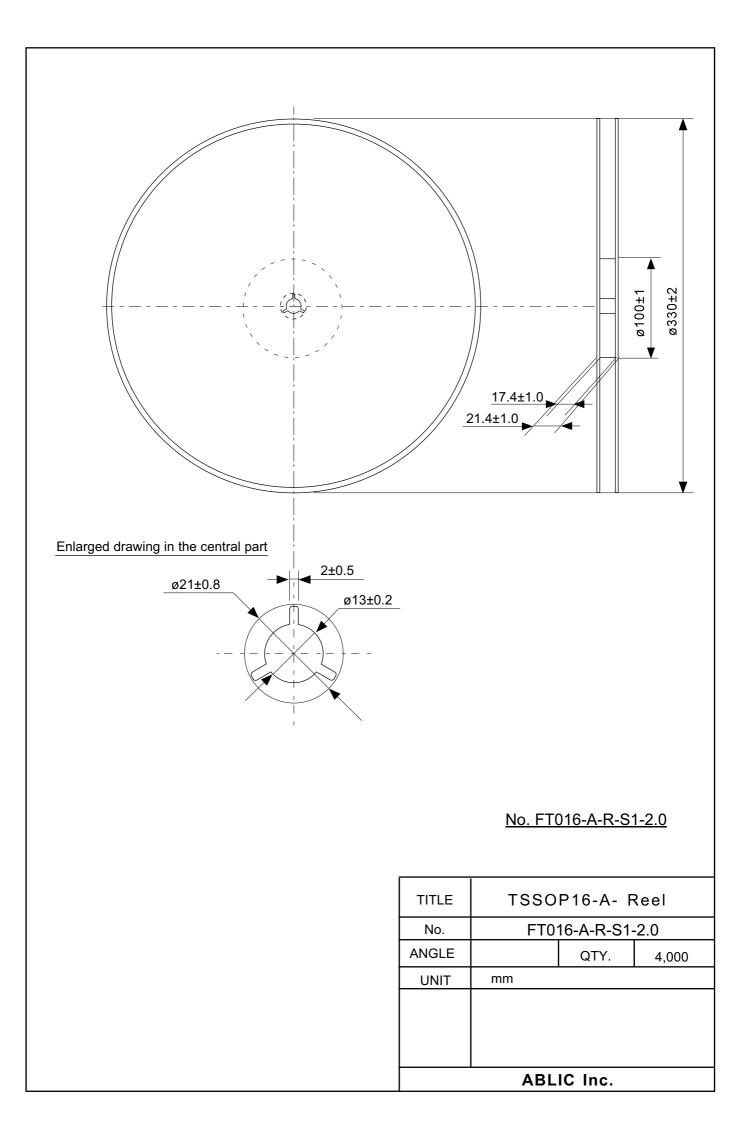


Item		Specification			
Size [mm]		114.3 x 76.2 x t1.6			
Material		FR-4			
Number of copper foil la	ayer	4			
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070			
	2	74.2 x 74.2 x t0.035			
	3	74.2 x 74.2 x t0.035			
	4	74.2 x 74.2 x t0.070			
Thermal via		-			

No. TSSOP16-A-Board-SD-1.0







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